

First‑Principles Study on the Structural, Elastic and Thermodynamic Properties of Binary Pd‑Sn Compounds

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Abstract

The structural, mechanical, thermodynamic and electronic properties of Pd-Sn compounds including $PdSn₁$, $PdSn₂$, $PdSn₃$, PdSn, Pd₂Sn and Pd₃Sn have been investigated by first-principles calculation. Results show that all of the Pd-Sn compounds considered here are thermodynamically and mechanically stable, ductile, elastic anisotropic and have low micro-hardness. Among them, Pd₂Sn is the most stable phase due to the lowest formation energy; PdSn exhibits the strongest anisotropy of the bulk modulus and shear modulus; Pd₃Sn shows the isotropy of bulk modulus according to the percentage bulk modulus calculation. Debye temperature and minimum thermal conductivity have approximately the same variation trend with the percentage of Pd where Pd_3Sn (or $PdSn_4$) has the highest (or lowest) Debye temperature and minimum thermal conductivity. The electronic density of states shows a strong hybridization of Pd-d with Sn-p electrons near the Fermi level, which has an important impact on the reliability of crystal. The three-dimensional (3D) charge density diference map shows ionic properties for these compounds, and the ionicity increases with Pd concentration according to the Bader charge analysis.

Keywords Intermetallics · phase stability · elastic properties · thermodynamic properties · frst-principles calculation

Introduction

In recent years, surface treatment technology, for example, the formation of surface-fnish Au/Pd/Ni(P) through electroless deposition of a submicron Pd flm on a Ni(P) pad, has become increasingly popular in the electronics industry.^{[1,](#page-11-0)[2](#page-11-1)} During the heat treatment process, the sandwiched Pd layer not only can improve the wettability but also can serve as an effective diffusion barrier layer^{[3,](#page-11-2)[4](#page-11-3)} to prevent the Ni(P) film from galvanic hyper-corrosion.^{[5](#page-11-4)[,6](#page-11-5)} Different types of Pd film can be produced by formic acid and alkaline hypophosphitebased solutions. Using formic acid electrolyte, a high-purity polycrystalline Pd flm can be formed. By exposure to alkaline hypophosphite conditions, amorphous Pd accompanied

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by 2–5 wt.% P dissolution can be obtained.^{[7](#page-11-6)} As is well known, Cu-based conductors are widely used as an interconnection with a Sn-based solder. However, the Cu-Sn compounds formed between the solder and conductor are brittle and possess high electrical resistivity, which deteriorates the electrical and mechanical properties of interconnection. To suppress the growth of Cu-Sn compounds, monolayer Ni or a heterojunction consisting of Au (or Pd) and a Ni layer is plated on the Cu-based conductor to form a sandwiched Au/ Ni/Cu (or Pd/Ni/Cu) conductor structure.^{[8](#page-11-7),[9](#page-11-8)} As a result, the reactive difusion occurs at the interface between Sn-based solder and Au (or Pd) during soldering. According to the literature, intermetallic compounds (IMCs) of $PdSn₄$ and $PdSn₃$ are formed through the room-temperature interaction between Pd and Sn.^{[10](#page-11-9)} Ni solid solution IMCs such as (Pd, $Ni)Sn₄$, (Pd, Ni)Sn₃ and (Pd, Ni)Sn₂ appear in (Pd-Ni)/Sn diffusion couple at 200° C.¹¹ A thinner intermetallic layer benefts the connection between the solder and substrate. However, the rapid and excessive growth of the compounds will have a deleterious effect on the mechanical reliability of solder joints due to their brittleness.

With the miniaturization of modern solder joints, the intermetallic layer will be proportionately thick. To some extent, the strength and reliability of solder joints are

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determined by the properties of intermetallics such as elastic, ductile or brittle transition, the thermal expansion and heat transfer coefficient. Based on the binary Pd-Sn phase diagram reported by Hultgren et al., 12 several compounds can exist, including Pd_3Sn , Pd_2Sn , $PdSn$, $PdSn_2$, $PdSn_3$ and PdSn₄. The compound Pd₂Sn exists at a low temperature but can decompose into $Pd₃Sn$ at a high temperature of 1193 K. The crystal structures of binary Pd-Sn compounds have been measured in experiment. For example, the compound Pd_3Sn , which belongs to the $Pm\bar{3}$ *m* space group, has the cubic structure of $Cu₃Au$ prototype with lattice parameters of $a=b=c=3.976 \text{ Å}$.^{13,14} The compound PdSn, which belongs to the space group *Pbnm*, has an orthorhombic structure of FeAs type with lattice parameters of $a = 6.126$, $b = 3.901$, $c = 6.480 \text{ Å}$.^{[15](#page-11-14)} Massalski assessed the Sn-rich corner of Pd-Sn ternary phase diagram and found four compounds (i.e., PdSn at 810 $^{\circ}$ C, PdSn₂ at 600 $^{\circ}$ C, PdSn₃ at 345 $^{\circ}$ C and PdSn₄ at 230 $^{\circ}$ C) in peritectic reactions.^{[16](#page-11-15)}

As mentioned above, Pd-Sn compounds have been reported in numerous studies. It is well known that the elastic and thermodynamic properties are important factors afecting the reliability of intermetallics appearing at the interconnected interfaces in the microelectronics industry. However, to date, no systematic research has been reported on the essential physical characteristics such as the bulk modulus, shear modulus, Young's modulus, thermodynamic and electronic properties for the binary Pd-Sn compounds. In view of this, further research is necessary. In our previous research, the physical properties of ternary compounds of (Pd, Ni)Sn₄ were successfully predicted.¹⁷ To enrich the database of physical characteristics of Pd-Sn systems, comprehensive investigations are carried out in this work to detect the intrinsic properties including the structural, elastic, thermodynamic and electronic characteristics. The related fndings are helpful to uncover the structural stability and mechanical properties of these intermetallics.

Calculation Details

Herein, we performed a first-principles calculation for the Pd-Sn-based intermetallics including $PdSn₄$, $PdSn₃$, PdSn₂, PdSn, Pd₂Sn and Pd₃Sn. The original structures used for geometry optimization, which are shown in Fig. [1,](#page-2-0) are derived from the inorganic crystal structure database $(ICSD).$ ^{[18–](#page-11-17)[21](#page-11-18)} The ground state lattice parameters are determined through the Vienna Ab initio Simulation Package (VASP) code. 22 The generalized gradient approximation (GGA) of Perdew-Burke-Ernzerhof (PBE) was treated as the exchange correlation function. The Monkhorst–Pack k-point meshes were used to evaluate Brillouin-zone integrations and electronic occupancies were determined according to the Methfessel–Paxton technique with 0.1 eV smearing.

The convergence threshold of total energy was set to less than 1×10^{-5} eV/atom. The valence electron configurations are treated with $5s^2 5p^2$ for Sn and $4d^{10}$ for Pd. During the structure optimization, full degrees of internal atomic coordinates are allowed to relax. After that, a static total energy calculation is performed to obtain the total energy of the crystal system.

Results and Discussion

Structure and Phase Stability

In calculation, all of the models are based on the experimental lattice constants obtained from the ICSD. The crystal structures and space groups of the considered binary Pd-Sn phases are displayed in Table [I.](#page-3-0) For convenient comparison, we listed the lattice parameters of those available in literature together with the results in this work. It is found that the geometric optimized lattice constants are all larger than the experimental results since the GGA method often overestimates the lattice parameters. In addition, the derived values of this calculation have very small errors compared to the experimental data, with the greatest deviation being less than 2%, indicating the reasonability of the computational method.

To detect the stability of the binary Pd-Sn compounds, formation energy ΔH is calculated based on the following equation.^{[17](#page-11-16)}

$$
\Delta H = [E_{Pd_x S n_y} - (x E_{Pd} + y E_{Sn})]/(x + y)
$$
\n(1)

Here, E_{Pd_x, Sn_y} is the total energy of Pd_xSn_y at the relaxed state, E_{Pd} and E_{Sn} are the per-atom energies of Pd with a facecentered cubic structure and β -Sn with a tetragonal structure in solid state, *x* and *y* is the number of Pd and Sn in the unit cell of $Pd_{x}Sn_{y}$, respectively. It is well known that a more negative formation energy is often accompanied by a better thermodynamically stable structure of the crystal system. The calculated formation energy along with the available literature values are listed in Table [I.](#page-3-0) Guadagno and Bryant el al. employed solution calorimetry to derive the formation energies of solid Pd-Sn alloys at 273 K and 320 K, respec-tively.^{[23,](#page-11-20)24} Using the direct synthesis calorimetry, Meschel derived the formation energy of $Pd₃Sn$ at room temperature.²⁵ The electromotive force method was used by Schaller to obtain the thermodynamic activity and Gibbs free energy of formation Pd_3Sn at a high temperature of 1173 K.²⁶ In the present work, the calculation is performed at zero temperature and zero pressure so as to predict the ground state properties of these compounds. It should be noted that the formation energy of -26.35 kJ/mol·atom for PdSn₄ by the frst-principles calculation was reported in our previous

Fig. 1 Crystal structures of binary Pd-Sn compounds (a) $PdSn_4$, (b) $PdSn_2$, (c) $PdSn_2$, (d) $PdSn_1$, (e) Pd_2Sn and (f) Pd_3Sn (tin atoms are large and gray, palladium atoms are small and navy) (Color fgure online).

work.[17](#page-11-16) This value is very close to Bryant's finding of −27.8 kJ/mol·atom through Sn solution calorimetry by the absolute deviation of 1.45 kJ/mol·atom. 24 Comparing our first-principles results of formation energy for $PdSn₂$ and PdSn with that of Guadagno, we found absolute errors of 2.46 kJ/mol·atom and 5.83 kJ/mol·atom, respectively. The small diference validates our calculation scheme. To visualize the variation trend, the relationship between the formation energy and the percentage composition of Pd is depicted in Fig. [2.](#page-3-1) All of the formation energies are negative, meaning that the structures of these Pd-Sn compounds are thermodynamically stable. Among them, $Pd₂Sn$ is the most thermodynamically stable structure due to the most negative formation energy of −55.12 kJ/mol·atom. The stability of PdSn and Pd_3Sn is slightly lower than Pd_2Sn on account of the corresponding formation energy of −54.47 kJ/mol·atom and -51.32 kJ/mol·atom, respectively. As for PdSn₄, the structure has relatively inferior stability owing to its higher formation energy than others. In fact, $PdSn₄$ commonly appears and is always accompanied by a high growth rate between the Sn-Ag-Cu solder with Pd surface fnish on the Ni/P pad.[11](#page-11-10) In view of this, we can reasonably assume that the considered Pd-Sn compounds in this work is easy to be formed between the solder and pad.

Elastic Property

Elastic constants are important factors owing to their close connection to the material's mechanical stability, stifness, anisotropy, ductility or brittleness. To detect the elastic constants of Pd-Sn compounds, a stress–strain method is used to calculate the elastic stiffness of the relevant phases. $27,28$ $27,28$

Table I The structural properties (including lattice constants (Å) and formation energy Δ*H* (kJ∕mol ∙ atoms)) for Pb–Sn IMCs in the present work and other references

Fig. 2 Variation in formation energy (unit: kJ/mol·atom) with the percentage of Pd atoms in Pd-Sn compounds.

A strain δ of less than 2% with a step of 0.005 was imposed on the optimized equilibrium crystals to determine the total energy change. The second-order elastic constants are derived through a polynomial ft of strain energy for specifc deformation.[29](#page-11-26) There are nine independent elastic constants in an orthorhombic crystal structure, which are C_{11} , C_{22} , C_{33} , C_{44} , C_{55} , C_{66} , C_{12} , C_{13} , C_{23} , while six are in the tetragonal crystal lattice, namely C_{11} , C_{33} , C_{44} , C_{66} , C_{12} , C_{13} , and three are in the cubic crystal lattice, namely C_{11} , C_{44} , C_{12} . The calculated elastic constants are displayed in Table [II](#page-4-0).

For orthorhombic crystal, the elastic constants should meet the mechanical stability criteria as follows:^{[30](#page-11-27)}

(2) C_{ii} > 0(*i* = 1 – 6); C_{11} + C_{22} > 2 C_{12} ; C_{22} + C_{33} > 2 C_{23} ; $C_{11} + C_{33} > 2C_{13}$; $C_{11} + C_{22} + C_{33} + 2C_{12} + 2C_{13} + 2C_{23} > 0$

For tetragonal crystal, the mechanical stability criteria are given by the expressions:

$$
C_{ii} > 0(i = 1, 3, 4, 6); C_{11} - C_{12} > 0;
$$

\n
$$
C_{11} + C_{33} - 2C_{13} > 0; 2(C_{11} + C_{12}) + C_{33} + 4C_{13} > 0
$$
\n(3)

For cubic crystal, the mechanical stability restrictions are given by the formula:

$$
C_{ii} > 0(i = 1, 4); C_{11} > |C_{12}|; C_{11} + 2C_{12} > 0.
$$
 (4)

Based on the single-crystal elastic constants listed in Table [II,](#page-4-0) all of the crystal structures satisfy the above criteria, which indicates that the binary Pd-Sn compounds considered in the present work are mechanically stable.

According to the single-crystal elastic constants, the polycrystalline elastic modulus such as the bulk modulus (*K*), shear modulus (*G*) and Young's modulus (*E*), which are often used to evaluate the material mechanical properties, can be derived through the Voigt-Reuss-Hill approxima-tion.^{[30,](#page-11-27)31} The bulk modulus *K* reflects the materials resistance to volume change under pressure. The shear modulus *G* gives an index of material resistance to plastic deformation such as shear strain. Young's modulus *E*, which is defned as the ratio of tensile stress to the corresponding tensile strain, can provide information on the stifness characteristics in solid. Generally speaking, a large Young's modulus often means high stifness. The calculated results on the polycrystalline elastic modulus are tabulated in Table [III,](#page-5-0) and their variation with the concentration of Pd is displayed in

Fig. [3](#page-4-1)a. It is found that Pd_3Sn has the largest values of bulk modulus, shear modulus and Young's modulus of 153. GPa, 53.1 GPa and 142.8 GPa, respectively, while $PdSn₄$ has the lowest bulk modulus, shear modulus and Young's modulus of 55.8 GPa, 21.3 GPa and 56.7 GPa, respectively. Therefore, it can be confirmed that $Pd₃Sn$ is not easily compressed and sheared and is a hard material among Pd-Sn compounds. According to Fig. [3](#page-4-1)a, we can see that the bulk modulus obviously increases with the concentration of Pd. But the shear modulus and Young's modulus no longer increase beyond a concentration of 25% (PdSn₃) and 66.7% (Pd₃Sn). Therefore, the shear modulus and Young's modulus follow the same increase order of PdSn₄, PdSn₂, PdSn₃, Pd₂Sn, PdSn and Pd₃Sn.

Poisson's ratio *ν* and *K/G* are often used to estimate the ductile or brittle properties of material. According to Poisson's ratio, a value of higher than 0.26 is associated with ductility and a value lower than 0.26 is accompanied by brit-tleness.^{[32,](#page-11-31)33} For K/G , dividing ductility from brittleness is 1.75. For example, if *K/G* is higher than 1.75, the material is ductile; otherwise it is brittle. Poisson's ratio can also be used to estimate the stability of a crystal against shear deformation. Material with a higher Poisson's ratio always expresses a better plasticity. The calculated Poisson's ratio

and *K/G* are listed in Table [IV](#page-5-1). Both Poisson's ratio and *K/G* are higher than 0.26 and 1.75, which means the Pd-Sn compounds involved in present work are ductile and plastic. The ductility increases in the order of $PdSn₄, PdSn₃, Pd₃Sn$, PdSn, PdSn₂, Pd₂Sn. The variation tendency of Poisson's ratio and *K/G* with Pd percentage are depicted in Fig. [3b](#page-4-1). It can be found that the degree of ductility almost increases with Pd concentration, except for PdSn and $Pd₃Sn$ due to their relatively lower Poisson ratio and *K/G*. In view of this, it can be deduced that Pd-Sn compounds formed on the surface between the solder and pad can serve as a good connection in the feld of electronics packaging.

The microhardness parameter *H*, which is another important factor used to detect the polycrystalline stifness, can be deduced from Poisson's ratio and Young's modulus based on the following equation. 31

$$
H = \frac{(1 - 2\nu)E}{6(1 + \nu)}
$$
 (5)

Generally speaking, a higher Young's modulus often accompanies a higher microhardness. The results of hardness are presented in Table [III](#page-5-0). It can be seen that, overall, the values of hardness are lower than 6 GPa, meaning the lower stiffness of the materials. Among them, $Pd₃Sn$ has the

Fig. 3 (a) The variation in the elastic modulus with the percentage of Pd atoms (unit: GPa), (b) the variation in Poisson's ratio and *K/G* with the percentage of Pd atoms in Pd-Sn compounds (dimensionless).

Table III The bulk modulus *K*, shear modulus *G*, Young's modulus *E* and microhardness *H* of Pd-Sn IMCs (units in GPa)

Poisson's ratio *v*, ratio of *K/G*, anisotropic factor, A_1 , A_2 , A_3 , universal anisotropy index *AU*, bulk anisotropic index A_K and shear anisotropic index *AG* (dimensionless) for the Pd-Sn IMCs

Table IV The results of

highest microhardness value while $PdSn₄$ has the lowest one, which is agreement with their Young's modulus.

Anisotropic Property

During the connection of solder with substrate, failure is often appeared at the interface due to the appearance of microcracks, holes and lattice distortion. The root cause is the crystalline anisotropic property. For example, crystals demonstrate diferent mechanical and thermodynamic properties in diferent directions. Research on the elastic anisotropy is benefcial to understand the mechanical durability of material. To quantitatively describe the elastic anisotropy, the anisotropic factors estimated from the elastic constants are used. 34 For orthorhombic crystal systems, there are three elastic anisotropic parameters:

$$
A_1 = \frac{4C_{44}}{C_{11} + C_{33} - 2C_{13}},
$$

\n
$$
A_2 = \frac{4C_{55}}{C_{22} + C_{33} - 2C_{23}},
$$

\n
$$
A_3 = \frac{4C_{66}}{C_{11} + C_{22} - 2C_{12}}
$$

\n(6)

For tetragonal crystal, two anisotropic factors are used:

$$
A_1 = \frac{2C_{66}}{C_{11} - C_{12}}, A_2 = \frac{2C_{44}}{C_{11} - C_{12}},
$$
\n(7)

For cubic crystal, only one is used:

$$
A_1 = \frac{2C_{44}}{C_{11} - C_{12}}\tag{8}
$$

If the value A_i (i = 1, 2, 3) is equal to 1, the crystal will show isotropic characteristics. Any value smaller or larger than 1 indicates anisotropy of crystal. The calculated anisotropic parameters are tabulated in Table [IV](#page-5-1). It can be seen that the Pd-Sn crystalline systems are all anisotropic.

Ranganathan et al. introduced a concept of universal elastic anisotropy index A_{U} , which is a measurement of the elas-tic anisotropy of the crystal with the following expression.^{[35](#page-12-1)}

$$
A_U = \frac{K_V}{K_R} + 5\frac{G_V}{G_R} - 6\tag{9}
$$

Here, K_{V} , K_{R} and G_{V} , G_{R} denote the bulk modulus and shear modulus according to the Voigt and Reuss scheme, respectively. A zero value of A_{U} indicates isotropic properties, and otherwise, anisotropic. The greater the value of A_U , the greater the mechanical anisotropy. The results of A_{U} displayed in Table [IV](#page-5-1) show that PdSn has the highest mechanical anisotropy, while $Pd₃Sn$ has the lowest universal mechanical anisotropy.

To visualize the anisotropic properties of these binary Pd-Sn compounds, the three-dimensional (3D) representations of elastic modulus with the crystallographic directions are depicted based on the single-crystal elastic constants in Fig. [4](#page-6-0). The derivation of formulas and calculation method for the orientation-dependent elastic modulus is discussed in detail in reference, 36 and hence it needs no further elaboration. In short, the 3D surface is spherical for an isotropic crystal, and anything other than a sphere indicates an anisotropic crystal. Obviously, the surfaces of the elastic moduli exhibit remarkable anisotropy for all of the Pd-Sn compounds. Among them, the shape of PdSn in Fig. [4d](#page-6-0) presents a dumbbell-shaped surface, suggesting the greatest

Fig. 4 Direction dependence of elastic modulus for Pd-Sn compounds: (a) $PdSn₄$, (b) $PdSn₃$, (c) $PdSn₂$, (d) $PdSn₂$, (e) $Pd₂Sn$, (f) $Pd₃Sn$ (unit: GPa).

anisotropy. This fnding is in good agreement with the calculation from the universal elastic anisotropy index A_{U} .

The percent elastic anisotropy factor such as A_K and A_G is another measurement of elastic anisotropy, which can be used to investigate the degree of elastic anisotropy in compression and shear modes.³⁷ Here, A_K and A_G are calculated through the following expressions.

$$
A_k = \frac{K_V - K_R}{K_V + K_R}, A_G = \frac{G_V - G_R}{G_V + G_R}
$$
(10)

A zero value of A_K and A_G always indicates isotropy, and any deviations indicate anisotropy. According to the results listed in Table [IV](#page-5-1), PdSn exhibits the strongest anisotropy of bulk modulus and shear modulus, with A_K of 13.45% and A_G of 29.34%. In contrast, Pd_3Sn shows isotropy of bulk modulus with a value of 0% and the lowest anisotropy of shear modulus with a value of 3.77%, in line with the previous conclusion from A_{U} . The variation in the anisotropic factors A_U , A_K and A_G with the concentration of Pd is shown in Fig. [5](#page-6-1). It is easy to see that the variation tendency of the percentage elastic anisotropy A_G is in good agreement with the trend of A_U , following the decreasing sequence of PdSn, PdSn₃, PdSn₂, PdSn₄, Pd₂Sn and Pd₃Sn.

Fig. 5 The variation in universal anisotropy index A_U , bulk anisotropic index A_K and shear anisotropic index A_G (dimensionless) with the percentage of Pd atoms in Pd-Sn compounds.

Heat Transfer Property

Intermetallics formed at the interface between a solder and substrate are critical for achieving a good connection. For a comprehensive understanding of the physical properties of the considered compounds, the heat transfer property is discussed in detail in present work. The Debye temperature is important for predicting the thermal conductivity. It has

been empirically established that a higher Debye temperature generally indicates better thermal conductivity. The Debye temperature can be deduced from the elastic wave velocity through the following equation.^{[32](#page-11-31)}

$$
\theta_D = \frac{h}{k_B} \left(\frac{3nN_A\rho}{4\pi M}\right)^{\frac{1}{3}} v_m \tag{11}
$$

Here, *h* is Planck's constant, k_B is Boltzmann's constant, N_A is Avogadro's constant, ρ is the density of the material, *M* is the molar mass, and *n* is the total number of atoms contained in the compound. The factor v_m is the averaged elastic wave velocity which is related to the transverse elastic wave velocity v_t and the longitudinal wave velocity v_t .

$$
v_m = \left[\frac{1}{3}\left(\frac{2}{v_t^3} + \frac{1}{v_l^3}\right)\right]^{-\frac{1}{3}}
$$
(12)

$$
v_t = \left(\frac{G}{\rho}\right)^{\frac{1}{2}}\tag{13}
$$

$$
v_l = \left(\frac{3K + 4G}{3\rho}\right)^{\frac{1}{2}}\tag{14}
$$

The calculated Debye temperature $\theta_{\rm D}$ together with the results of the density ρ , transverse elastic wave velocity v_t , longitudinal elastic wave velocity v_1 and average wave velocity v_m are all listed in Table [V](#page-7-0). It can be seen that Pd_3Sn has the highest Debye temperature, while $PdSn₄$ has the lowest. Pd₂Sn has a Debye temperature lower than PdSn, but higher than $PdSn_3$ and $PdSn_2$ in sequence.

Since the material's heat transfer ability will decrease with increasing temperature at high temperature, 38 it is meaningful to explore the minimum thermal conductivity at high temperature to evaluate the material's application under extreme conditions. To quantitatively clarify the lower limit of thermal conductivity

at high temperature, Clarke's model³⁸ and Cahill's model^{39,40} are used through the following expressions in sequence

$$
k_{\min}^a = 0.87 k_B M_a^{-\frac{2}{3}} E^{\frac{1}{2}} \rho^{\frac{1}{6}}
$$
 (15)

$$
k_{\min}^b = \frac{k_B}{2.48} n \vec{r}^{\frac{2}{3}} (2v_t + v_l) \tag{16}
$$

Here, k_B and ρ have the same meaning as in Eq. [11](#page-7-1). The average mass M_a per atom can be obtained from $M_a = \frac{M}{nN_A}$ where *n* and *M* are those in Eq. [11](#page-7-1). The parameter *E* stands for the Young's modulus. In Eq. [16,](#page-7-2) *n*′ is the number of atoms per unit volume, which can be derived from $n' = \frac{\rho}{M_a}$, v_t and v_l are the transverse and longitudinal elastic wave velocities, respectively. The calculated values of k_{min}^a from Clarke's model and k_{min}^b from Cahill's model are also displayed in Table [V.](#page-7-0) Since the contribution from the optical phonon cannot be considered, Clarke's model often gives a lower estimate for the thermal conductivity than Cahill's model.[40](#page-12-6) Researchers have suggested that the lowest thermal conductivity from Cahill's model is more accurate than Clarke's model due to its atomic number density and phonon spectrum.⁴⁰ It is found that the values of k_{min}^a and k_{min}^b roughly increase with Pd concentration except for $Pd₂Sn$ due to its slightly lower value of k_{min}^a than that for PdSn. For convenience, the variation in Debye temperature and k_{min} with the concentration of Pd is plotted in Fig. [6.](#page-8-0) It can be seen that the decreasing trend of k_{min} is roughly the same as that of Debye temperature. Through comparison, the values of k_{min}^a rank in decreasing order of Pd₃Sn, PdSn, Pd₂Sn, PdSn₂, PdSn₃ and PdSn₄. Debye temperature θ_D decreases in the order of Pd_3Sn , PdSn, Pd_2Sn , $PdSn_3$, $PdSn_2$ and PdSn₄. The slight difference in PdSn₃ and PdSn₂ is caused by the anisotropy of crystals, which can be refected from the 3D surface map as in Fig. [4](#page-6-0) and the universal elastic anisotropy index A_U . To be specific, the 3D shape of $PdSn_3$ in Fig. [4b](#page-6-0) presents many convex regions, while that of $PdSn₂$

Table V The density ρ (in kg/m³), transverse elastic wave velocity v_r , longitudinal elastic wave velocity v_l , average elastic wave velocity v_m (in m/s), Debye temperature θ_D (in K) and minimum thermal conduc-

tivity k_{min}^a of Clarke's model and k_{min}^b of Cahill's model (in W/m K) for the Pd-Sn IMCs

IMCs	D	v_{t}	ν,	v_m	θ_D	k_{min} ^a	k_{min} ^b
PdSn ₄	7788.45	1653.73	3287.40	1854.51	189.47	0.381	0.432
PdSn ₃	8094.56	1721.90	3490.13	1933.15	200.41	0.410	0.467
PdSn ₂	8487.76	1611.06	3633.10	1818.15	194.69	0.415	0.493
PdSn	9414.57	1834.97	3892.79	2065.08	227.17	0.495	0.574
Pd_2Sn	10612.22	1624.34	3987.47	1838.91	211.82	0.488	0.602
Pd_3Sn	11056.61	2191.47	4502.05	2462.16	288.41	0.667	0.764

in Fig. [4](#page-6-0)c shows a sunken area, which means that the anisotropic degree of $PdSn_3$ is higher than $PdSn_2$. Furthermore, $PdSn₃$ has a higher value of universal elastic anisotropy index A_{U} of 2.6987, while PdSn₂ has a lower A_{U} of 1.7975 (see Table [IV\)](#page-5-1). Among the Pd-Sn compounds considered, Pd_3Sn has the highest values of Debye temperature and k_{min} , while $PdSn₄$ has the lowest values. From this point of view, our fnding is fairly consistent with the literature, in which higher Debye temperature is often accompanied by higher minimum thermal conductivity. 41 Thus, the intrinsic thermal

Fig. 6 The variation in Debye temperature θ_p (in K) and minimum thermal conductivity k_{min} (in W/m K, k_{min}^{\dagger} of Clarke's model and k_{\min} ^b of Cahill's model) with the percentage of Pd atoms in Pd-Sn compounds.

properties of the Pd-Sn compound are obtained, which can provide a useful reference for the surface treatment process of solder with pad.

Electronic Structure

To illustrate the chemical bonding character for the Pd-Sn compounds, the total density of states (TDOS) and partial density of states (PDOS) are considered, which are depicted in Fig. [7](#page-8-1). The six IMCs are all metallic due to a non-zero density of states at the Fermi-level. Through the TDOS, we can see that the contribution to the TDOS at the lower energy range from about -10.8 eV to -5.4 eV for PdSn₄, -11.3 eV to -5.6 eV for PdSn₃, -10.8 eV to -5.8 eV for PdSn₂, -10.9 eV to -6.9 eV for PdSn, is dominated mainly by the Sn-s states together with some Pd-d and Sn-p states. For Pd₂Sn and Pd₃Sn, the low-lying states from -10.6 to −7.7 eV and −9.9 eV to −7.8 eV are driven mainly by Sn-s sates and some Pd-d states, and the Sn-p electrons made scarcely any contribution to the TDOS. Specifcally, we focus more on the states near the Fermi level because the electrons nearby have more impact on material properties such as reliability. At the higher energy range from about −4.9 eV to −2.7 eV for PdSn4, −5.5 eV to −2.4 eV for PdSn₃, PdSn₂ and PdSn, -6.0 eV to -1.9 eV for Pd₂Sn and -5.9 eV to 0 eV for Pd₃Sn, most of the Pd-d states dominated with some Sn-p electrons as the main contributors to the TDOS, meaning a hybridization of Pd-d with Sn-p electrons. Above the Fermi level, Sn-p electrons are the main contributors to the TDOS for $PdSn₄$, $PdSn₃$, $PdSn₂$ and $PdSn$.

Fig. 7 TDOS and PDOS for binary Pd-Sn compounds: (a) $PdSn_4$, (b) $PdSn_3$, (c) $PdSn_2$, (d) $PdSn$, (e) Pd_2Sn , (f) Pd_3Sn . (The dashed lines at 0 eV denote the Fermi level E_f).

Fig. 8 Charge density diference for binary Pd-Sn compounds: (a) PdSn₄, (b) PdSn₃, (c) PdSn₂, (d) PdSn, (e) Pd₂Sn, (f) Pd₃Sn (unit: e/ \mathring{A}^3 ; a red isosurface represents negative charge density and a yellow

isosurface represents positive charge density, with a maximum value of 0.004 $e/\text{\AA}^3$; tin atoms are large and gray, palladium atoms are small and navy) (Color fgure online).

For Pd₂Sn, both the Sn-p and Pd-d electrons are the main contributors to the TDOS, indicating a strong hybridization of Sn-p with Pd-d electrons, while for Pd_3Sn , Pd-d electrons are the main contributors for the TDOS, which are slightly hybridized with some Sn-p electrons, meaning a relatively weak hybridization of Pd-d and Sn-p electrons. With the increasing concentration of Pd in Pd-Sn compounds such as PdSn, Pd_2Sn and Pd_3Sn , the dominant Pd-d electrons is increasingly obvious in the TDOS near Fermi level. The interactions of Pd-d electrons together with the hybridization

of Pd-d with Sn-p electrons form more stable bonds, leading to more stable structures, which is in agreement with the finding that the compounds of PdSn, Pd_2Sn and Pd_3Sn have relatively more stable structures among Pd-Sn compounds from the results of formation energy.

To further reveal the bonding mechanism of the Pd-Sn compounds, a 3D charge density diference map is given in Fig. [8](#page-9-0) where the yellow and red isosurfaces represent the enrichment and dissipation regions of charge density, respectively. A signifcant depletion of the charge density at the atom sites along with an accumulation of the charge density in the interstitial region can be found, which means ionic bonding of these Pd-Sn compounds. In Fig. [8](#page-9-0)f, the enrichment region of charge density has a typical annular shape, which means a strong ionic bonding of Pd and Sn.

To explore the electronegativity in depth and quantify the charge distribution, Bader charge analysis $42,43$ $42,43$ is used with the detailed information listed in Table [VI.](#page-10-0) The effective valence charge q can be obtained from the Bader charge minus the formal charge. The positive value of efective valence charge means the received amount of charge while the negative value means the lost amount. We grouped the same type of Bader charges with the overlapped number *n* for the Pd-Sn compounds. It can be found from Table [VI](#page-10-0) Sn atoms are lost charges while Pd atoms are gained, which means Sn transferred charges to Pd. The number of transferred charges per Sn is 0.194 for PdSn₄, 0.229 for PdSn₃, 0.329 for PdSn₂, 0.545 for PdSn, 0.669 for Pd_2 Sn and 0.849 for Pd_3 Sn. So the ionicity of these compounds increases with Pd concentration in the sequence $PdSn_4 < PdSn_3 < PdSn_2 < PdSn < Pd_2Sn < Pd_3Sn$.

Conclusions

First-principles calculations were used to investigate the structure, phase stability, mechanical, thermodynamic and electronic properties of the binary Pd-Sn compounds (PdSn₄, PdSn₃, PdSn₂ PdSn, Pd₂Sn and Pd₃Sn). The optimized lattice parameters accord well with the literature fndings. Six compounds are all thermodynamically and elastically stable. Among them, $Pd₂Sn$ is the most stable phase mainly due to a strong hybridization of Pd-d with Sn-p electrons near the Fermi level according to the PDOS. The polycrystalline elastic modulus and anisotropic characters are derived. Pd_3Sn has the largest values of bulk modulus, shear modulus and Young's modulus while $PdSn₄$ has the lowest values. The shear modulus and Young's modulus follow the increasing order of $PdSn₄$, $PdSn₃$, $PdSn₃$, $Pd₂Sn$, PdSn and Pd_3 Sn. The microhardness parameters show that they are all low-stifness materials. The Pd-Sn compounds are all ductile and anisotropic. Ductility increases with Pd concentration. Among the six compounds, PdSn exhibits the strongest anisotropy of the bulk modulus and shear modulus, while Pd_3Sn shows an isotropy of bulk modulus according to the percentage bulk modulus calculation. The heat transfer property is predicted using the Debye temperature and Clarke's model and Cahill's model. The minimum thermal conductivity of k_{min}^a and k_{min}^b roughly increases with Pd concentration, with a value of k_{min}^a lower than k_{min}^b . The Debye temperature decreases in the order of $Pd₃Sn$, $PdSn$, Pd₂Sn, PdSn₃, PdSn₂ and PdSn₄, and k_{min}^a decreases in the order of Pd₃Sn, PdSn, Pd₂Sn, PdSn₂, PdSn₃ and PdSn₄. The slight difference in order of θ_D and k_{min}^a between $PdSn_3$ and $PdSn₂$ is discussed based on the anisotropic property. All of the compounds performed ionic bonding from the charge density diference map, and the ionicity increased with Pd concentration according to the Bader charge analysis.

The mechanical and thermal properties are calculated in this work. The results cannot be compared due to the absence of any reported data. Therefore, these results can be used as a prediction and good reference for the future application of the material.

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Conflict of interest The authors declare that they have no confict of interest.

References

- 1. J. Kim, S.B. Jung, and J.W. Yoon, Efects of a phosphorous-containing Pd layer in a thin-ENEPIG surface fnish on the interfacial reactions and mechanical strength of a Sn-58Bi solder joint. *J. Alloys Compd.* 820, 153396 (2020).
- 2. C.E. Ho, L.H. Hsu, C.H. Yang, T.C. Yeh, and P.T. Lee, Efect of Pd (P) thickness on the soldering reaction between Sn-3Ag-0.5 Cu alloy and ultrathin-Ni (P)-type Au/Pd (P)/Ni (P)/Cu metallization pad. *Thin Solid Films* 584, 257 (2015).
- 3. Y.W. Yen, P.H. Tsai, Y.K. Fang, S.C. Lo, Y.P. Hsieh, and C.I. Lee, Interfacial reactions on Pb-free solders with Au/Pd/Ni/Cu multilayer substrates. *J. Alloys Compd.* 503, 25 (2010).
- 4. J.W. Yoon, B.I. Noh, J.H. Yoon, H.B. Kang, and S.B. Jung, Sequential interfacial intermetallic compound formation of $Cu₆Sn₅$ and $Ni₃Sn₄$ between Sn-Ag-Cu solder and ENEPIG substrate during a refow process. *J. Alloys Compd.* 509, 153 (2011).
- 5. K. Zeng, R. Stierman, D. Abbott, and M. Murtuza, The root cause of black pad failure of solder joints with electroless Ni/immersion gold plating. *JOM* 58, 75 (2006).
- 6. K. Suganuma and K.S. Kim, The root causes of the "black Pad" phenomenon and avoidance tactics. *JOM* 60, 61 (2008).
- 7. S.P. Peng, W.H. Wu, C.E. Ho, and Y.M. Huang, Comparative study between Sn37Pb and Sn3Ag0.5Cu soldering with Au/Pd/ Ni (P) tri-layer structure. *J. Alloys Compd.* 493, 431 (2010).
- 8. Y.S. Wu, P.T. Lee, W.Z. Hsieh, T.T. Kuo, and C.E. Ho, Interfacial reaction and mechanical reliability between Sn-3Ag-0.5Cu alloy and ultrathin-Ni(P)-type Au/Pd(P)/Ni(P)/Cu metallization pad. *Surf. Coat. Technol.* 359, 374 (2019).
- 9. C.Y. Lee, S.P. Yang, C.H. Yang, M.K. Lu, T.T. Kuo, and C.E. Ho, Infuence of Pd(P) thickness on the Pd-free solder reaction between eutectic Sn-Ag alloy and Au/Pd(P)/Ni(P)/Cu multilayer. *Surf. Coat. Technol.* 395, 1 (2020).
- 10. V. Simić and Z. Marinković, Room temperature interactions in Pd-metal thin flm couples. *Mater. Chem. Phys.* 47, 246 (1997).
- 11. M.A. Rahman, C.E. Ho, W. Gierlotka, and J.C. Kuo, Experimental determination and thermodynamic modeling of the Sn-Rich corner of the ternary Ni-Pd-Sn phase diagram at 250℃. *J. Electron. Mater.* 43, 4582 (2014).
- 12. R. Hultgren, P.D. Desai, D.T. Hawkins, M. Gleiser, K.K. Kelley, and D.D. Wagman, *Selected Values of the Thermodynamic Properties of the Elements* (OH: American Society for Metals, 1973).
- 13. K.L. Shelton, P.A. Merewether, and J. Skinner, Phases and phase relations in the system palladium-platinum-tin. *Can. Mineral.* 19, 599 (1981).
- 14. I.R. Harris, M. Norman, and A.W. Bryant, A study of some palladium-indium, platinum-indium and platinum-tin alloys. *J. Less Common. Met.* 16, 427 (1968).
- 15. M.A. Kareva, E.G. Kabanova, G.P. Zhmurko, V.N. Kuznetsov, and A.V. Yatsenko, Phases of the NiAs family in Cu-Pd-Sn and Au-Pd-Sn systems. *Russ. J. Inorg. Chem.* 57, 502 (2012).
- 16. T.B. Massalski, *Binary Alloy Phase Diagrams* (OH: American Society for Metals, 1990), pp. 3049–3051.
- 17. Y.L. Tian, L.F. Zhang, and P. Wu, First-principles study of structural, elastic, and thermodynamic properties of $PdSn₄$ with Ni addition. *J. Electron. Mater.* 49, 1435 (2020).
- 18. R. Kubiak and M. Wolcyrz, Refnement of the crystal structures of AuSn4 and PdSn4. *J. Less Common Metals* 97, 265 (1984).
- 19. K. Schubert, H.L. Lukas, H.G. Meissner, and S. Bhan, Pd5Sn7— A novel binary stannide in Pd-Sn system. *Z. Metallkd.* 50, 534 (1959).
- 20. J. Nylén, F.G. Garcıa, B.D. Mosel, R. Pöttgen, and U. Häussermann, Structural relationships, phase stability and bonding of compounds PdSnn (n= 2, 3, 4). *Solid State Sci.* 6, 147 (2004).
- 21. K. Schubert, H.L. Lukas, H.G. Meissner, and S. Bhan, Structure of the systems cobalt- gallium, palladium-gallium, palladium-tin, and related alloys. *Z. Metallkd.* 50, 534 (1959).
- 22. G. Kresse and J. Furthmüller, Efficient iterative schemes for ab initio total-energy calculations using a plane-wave basis set. *Phys. Rev. B* 54, 11169 (1996).
- 23. J.R. Guadagno and M.J. Pool, Liquid palladium-tin alloys. *J. Phys. Chem.* 72, 2535 (1968).
- 24. A.W. Bryant, W.G. Bugden, and J.N. Pratt, Calorimetric and galvanic cell studies of the thermodynamic properties of palladiumtin alloys. *Acta Metall.* 18, 101 (1970).
- 25. S.V. Meschel and O.J. Kleppa, Standard enthalpies of formation of some 3d, 4d and 5d transition-metal stannides by direct synthesis calorimetry. *Thermochim. Acta* 314, 205 (1998).
- 26. H.-J. Schaller and H. Brodowsky, Thermodynamic Properties of Pd-Sn Alloys. *Z. Metallkd.* 69, 87 (1978).
- 27. Y.F. Wu, B. Wu, and Z.Y. Wei, Structural, half-metallic and elastic properties of the half-Heusler compounds N_iM_nM ($M = S_b$, As and Si) and IrMnAs from frst-principles calculations. *Intermetallics* 53, 26 (2014).
- 28. W. Zhou, L.J. Liu, B.L. Li, and P. Wu, Structural, elastic and electronic properties of intermetallics in the Pt-Sn system: a density functional investigation. *Comput. Mater. Sci.* 46, 921 (2009).
- 29. W.C. Hua, Y.A. Liu, D.J. Li, and H.L. Jin, Structural, anisotropic elastic and electronic properties of Sr-Zn binary system intermetallic compounds: a frst-principles study. *Comput. Mater. Sci.* 99, 381 (2015).
- 30. J.L. Du, B. Wen, R. Melnik, and Y. Kawazoe, Phase stability, elastic and electronic properties of Cu-Zr binary system intermetallic compounds: a frst-principles study. *J. Alloys Compd.* 588, 96 (2014).
- 31. H.-C. Cheng, C.-F. Yu, and W.-H. Chen, First-principles density functional calculation of mechanical, thermodynamic and electronic properties of CuIn and Cu₂In crystals. *J. Alloys Compd.* 546, 286 (2013).
- 32. X. Zhang, C. Ying, Z. Li, and G. Shi, First-principles calculations of structural stability, elastic, dynamical and thermodynamic properties of SiGe, SiSn GeSn. *Superlattices Microstruct.* 52, 459 (2012).
- 33. C.M. Li, S.M. Zeng, and Z.Q. Chen, First-principles calculations of elastic and thermodynamic properties of the four main intermetallic phases in Al-Zn-Mg-Cu alloys. *Comp. Mater. Sci.* 93, 210 (2014).
- 34. M. Tao, Z.R. Wang, and C.X. Lan, Exploring phase stability, electronic and mechanical properties of Ce-Pb intermetallic compounds using frst-principles calculations. *J. Solid State Chem.* 237, 385 (2016).
- 35. S.I. Ranganathan and M. Ostoja-Starzewskl, Universal elastic anisotropy index. *Phys. Rev. Lett.* 101, 055504 (2008).
- 36. J.Y. Wu, B. Zhang, and Y.Z. Zhan, Ab initio investigation into the structure and properties of Ir-Zr intermetallics for high-temperature structural applications. *Comput. Mater. Sci.* 131, 146 (2017).
- 37. Y. Liu, X. Chong, Y. Jiang, R. Zhou, and J. Peng, Mechanical properties and electronic structures of Fe-Al intermetallic. *Phys. B Condens. Matter* 506, 1 (2017).
- 38. D.R. Clarke and C.G. Levi, Materials design for the next generation thermal barrier coatings. *Annu. Rev. Mater. Res.* 33, 383 (2003).
- 39. D.G. Cahill, S.K. Watson, and R.O. Pohl, Lower limit to the thermal conductivity of disordered crystals. *Phys. Rev. B* 46, 6131 (1992).
- 40. Y.H. Duan, Y. Sun, and L. Lu, Thermodynamic properties and thermal conductivities of $TiAl₃$ -type intermetallics in Al-Pt-Ti system. *Comput. Mater. Sci.* 68, 229 (2013).
- 41. H.C. Deng, Theoretical prediction of the structural, electronic, mechanical and thermodynamic properties of the binary α -As₂Te₃ and β-As₂Te₃. *J. Alloys Compd.* 656, 695 (2016).
- 42. R.F.W. Bader, *Atoms in Molecules: A Quantum Theory* (New York: Oxford University Press, 1990).
- 43. G. Henkelman, A. Arnaldsson, and H. Jonsson, A fast and robust algorithm for Bader decomposition of charge density. *Comput. Mater. Sci.* 36, 254 (2006).

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